## REMARKS

Responsive to the requirement for restriction, applicant elects Group I, claims 1-16, drawn to a semiconductor device/system, without traverse.

Non-elected claims 17-19 and 29-32 are canceled herewith, but may be made the subject of a divisional application to be filed at any time during the pendency of the present application.

Also, claims 20-28 are canceled and are being made the subject of a divisional application to be filed soon.

Responsive to the requirement for election of species, applicant elects that of Fig. 1. It is believed that all the claims are readable on the elected embodiment, and a paper that accompanies this amendment, headed "Attachment-1", shows the readability of claim 1 on the various figures.

An action on the merits is respectfully requested.

The Commissioner is hereby authorized in this, concurrent, and future replies, to charge payment or credit any

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overpayment to Deposit Account No. 25-0120 for any additional fees required under 37 C.F.R. § 1.16 or under 37 C.F.R. § 1.17.

Respectfully submitted,

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## APPENDIX:

	The Appendix includes the following item(s):
<u> </u>	a terminal disclaimer
□ -	a 37 CFR 1.132 Declaration
□ -	a new or amended Abstract of the Disclosure
□ -	a Replacement Sheet for Figure of the drawings
	a Substitute Specification and a marked-up copy of the originally-filed specification
□ -	a verified English translation of foreign priority
docur	ment
፟ -	Attachment-1



## Attachment-1

Elements of Claim 1	Fig. 1	Fig. 2	Fig. 3
Inter layer dielectric film having Si-H bonds	103, 109, 115	203, 214	303, 309, 312
A base layer including a semiconductor substrate	101	201	301
Silicon carbon nitride film formed on the interlayer dielectric film	108, 114, 120	208, 213, 219	308, 311, 317